CY62127BV MoBL®

1M (64K x 16) Static RAM

Features

- **High Speed: 55 ns and 70 ns**
- **Wide voltage range: 2.7V–3.6V**
- **Low active power**
  - **— 54 mW (max.) (15 mA)**
- **Low standby power (70 ns)**
  - **— 54 µW (max.) (15 µA)**
- **Easy memory expansion with $\overline{CE}$ and $\overline{OE}$ features**
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**
- **Package available in a 44-pin TSOP Type II (forward pinout) and a 48-ball fBGA package**

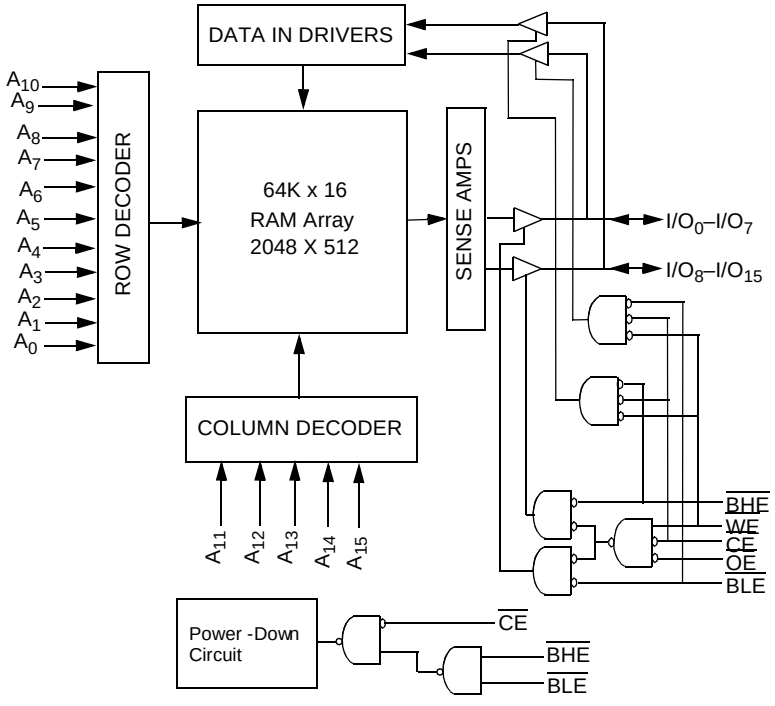
Functional Description[1]

The CY62127BV MoBL® MoBL® is a high-performance CMOS static RAM organized as 64K words by 16 bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL) in portable applications such as cellular telephones. The device also has an automatic power-down feature that significantly reduces power consumption when addresses are not toggling, or when deselected ($\overline{CE}$ HIGH or both $\overline{BLE}$ and $\overline{BHE}$ are HIGH). The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when: deselected ($\overline{CE}$ HIGH), outputs are disabled ($\overline{OE}$ HIGH), both Byte High Enable and Byte Low Enable are disabled ($\overline{BHE}$, $\overline{BLE}$ HIGH), or during a write operation ($\overline{CE}$ LOW, and $\overline{WE}$ LOW).

Writing to the device is accomplished by taking Chip Enable ($\overline{CE}$) and Write Enable ($\overline{WE}$) inputs LOW. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from I/O pins (I/O_1 through I/O_8), is written into the location specified on the address pins (A_0 through A_{15}). If Byte High Enable ($\overline{BHE}$) is LOW, then data from I/O pins (I/O_9 through I/O_{16}) is written into the location specified on the address pins (A_0 through A_{15}).

Reading from the device is accomplished by taking Chip Enable ($\overline{CE}$) and Output Enable ($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7. If Byte High Enable ($\overline{BHE}$) is LOW, then data from memory will appear on I/O_8 to I/O_{15}. See the truth table at the back of this data sheet for a complete description of read and write modes.

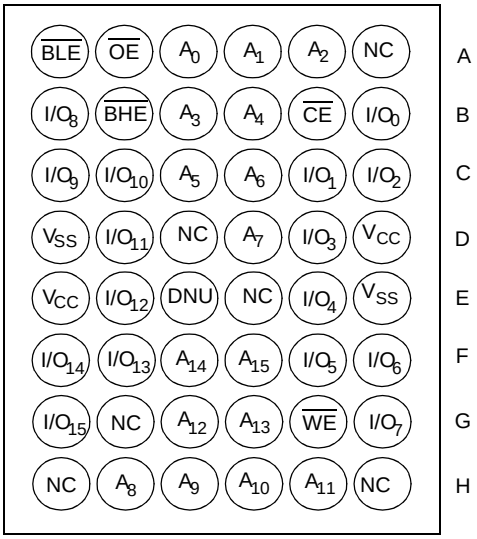
Logic Block Diagram



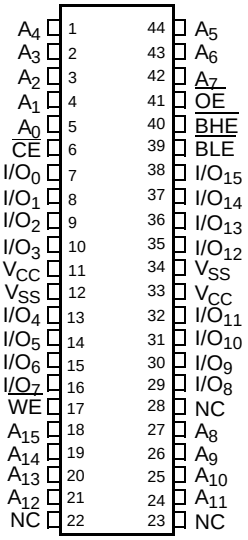
Note:
1. For best practice recommendations, please refer to the Cypress application note "System Design Guidelines" on http://www.cypress.com.

Pin Configurations[2]

FBGA (Top View)



TSOP II (Forward) Top View



Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature .....–65°C to +150°C

Ambient Temperature with Power Applied.....–55°C to +125°C

Supply Voltage to Ground Potential ..... –0.5V to 4.6V

DC Voltage Applied to Outputs in High-Z State[3] .....–0.5V to V_{CC} + 0.5V

DC Input Voltage[3]..... –0.5V to V_{CC} + 0.5V

Output Current into Outputs (LOW)..... 20 mA

Static Discharge Voltage..... >2001V (per MIL-STD-883, Method 3015)

Latch-up Current..... >200 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Industrial	–40°C to +85°C	2.7V to 3.6V

Product Portfolio

Product	V_{CC} Range (V)			Speed (ns)	Power Dissipation (Industrial)		
					Operating, I_{CC} (mA) f = f_{max}	Standby, I_{SB2} (µA)	
	$V_{CC(min.)}$	$V_{CC(typ.)}$[4]	$V_{CC(max.)}$		Max.	Typ.[4]	Max.
CY62127BV MoBL®	2.7	3.0	3.6	55	20	0.5	15
				70	15		

Notes:
2. NC pins are not connected to the die.
3. $V_{IL(min.)}$ = –2.0V for pulse durations less than 20 ns.
4. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = $V_{CC(typ.)}$, T_A = 25°C.

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions		CY62127BV MoBL®-55 Min.	CY62127BV MoBL®-55 Typ.[4]	CY62127BV MoBL®-55 Max.	CY62127BV MoBL®-70 Min.	CY62127BV MoBL®-70 Typ.[4]	CY62127BV MoBL®-70 Max.	Unit
V_{OH}	Output HIGH Voltage	I_{OH} = –1.0 mA	V_{CC} = 2.7V	2.2			2.2			V
V_{OL}	Output LOW Voltage	I_{OL} = 2.1 mA	V_{CC} = 2.7V			0.4			0.4	V
V_{IH}	Input HIGH Voltage			2.0		V_{CC} + 0.3V	2.0		V_{CC} + 0.3V	V
V_{IL}	Input LOW Voltage			–0.3		0.4	–0.3		0.4	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}		–1		+1	–1		+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_I ≤ V_{CC}, Output Disabled		–1		+1	–1		+1	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{MAX} = $1/t_{RC}$	V_{CC} = 3.6V, I_{OUT} = 0 mA, CMOS Levels			20			15	mA
I_{SB1}	Automatic CE Power-Down Current— TTL Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{IH}, V_{IN} ≥ V_{IH} or V_{IN} ≤ V_{IL}, f = f_{MAX}				2			2	mA
I_{SB2}	Automatic CE Power-Down Current— CMOS Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{CC} – 0.3V, V_{IN} ≥ V_{CC} – 0.3V, or V_{IN} ≤ 0.3V, f = 0			0.5	15		0.5	15	µA

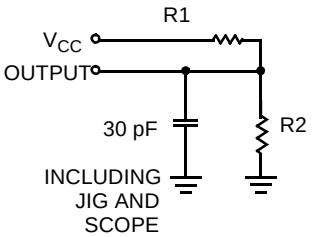
Capacitance[5]

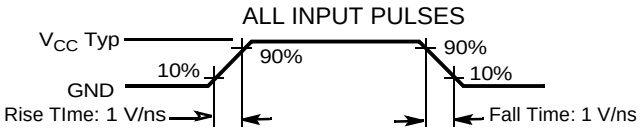
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = 3.3V	9	pF
C_{OUT}	Output Capacitance		9	pF

Thermal Resistance

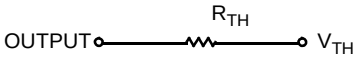
Description	Test Conditions	Symbol	BGA	Unit
Thermal Resistance (Junction to Ambient)[5]	Still Air, soldered on a 4.25 x 1.125 inch, 4-layer printed circuit board	Θ_{JA}	55	°C/W
Thermal Resistance (Junction to Case)[5]		Θ_{JC}	16	°C/W

AC Test Loads and Waveforms





Equivalent to: THÉVENIN EQUIVALENT



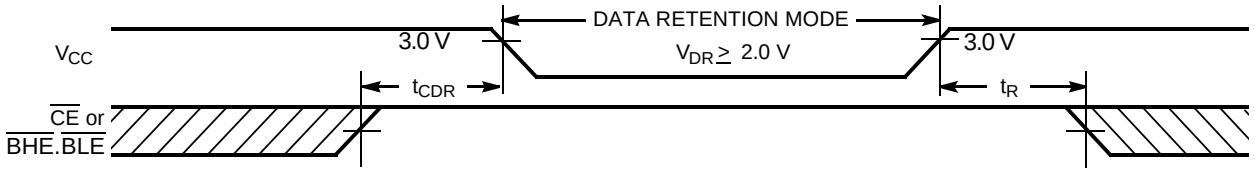
Note:
5. Tested initially and after any design or process changes that may affect these parameters.

Parameters	3.0V	Unit
R1	1.076	K Ohms
R2	1.262	K Ohms
R_{TH}	0.581	K Ohms
V_{TH}	1.620	Volts

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions	Min.	Typ.[4]	Max.	Unit
V_{DR}	V_{CC} for Data Retention		2.0		3.6	V
I_{CCDR}	Data Retention Current	V_{CC}= V_{DR} = 2.0V, $\overline{CE} \geq V_{CC} - 0.3V$, $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$		0.5	15	µA
t_{CDR}[5]	Chip Deselect to Data Retention Time		0			ns
t_R[6]	Operation Recovery Time		t_{RC}			ns

Data Retention Waveform[7]



Switching Characteristics Over the Operating Range [8]

Parameter	Description	55 ns		70 ns		Unit
		Min.	Max.	Min.	Max.	
Read Cycle						
t_{RC}	Read Cycle Time	55		70		ns
t_{AA}	Address to Data Valid		55		70	ns
t_{OHA}	Data Hold from Address Change	10		10		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		55		70	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		25		35	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z[9]	5		5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[9, 11]		20		25	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[9]	10		10		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[9, 11]		20		25	ns
t_{PU}	$\overline{CE}$ LOW to Power-Up	0		0		ns
t_{PD}	$\overline{CE}$ HIGH to Power-Down		55		70	ns
t_{DBE}	$\overline{BHE}$ / $\overline{BLE}$ LOW to Data Valid		55		70	ns
t_{LZBE}[10]	$\overline{BHE}$ / $\overline{BLE}$ LOW to Low Z[9]	5		5		ns
t_{HZBE}	$\overline{BHE}$ / $\overline{BLE}$ HIGH to High Z[9, 11]		20		25	ns
Write Cycle[12]						
t_{WC}	Write Cycle Time	55		70		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	45		60		ns

Notes:

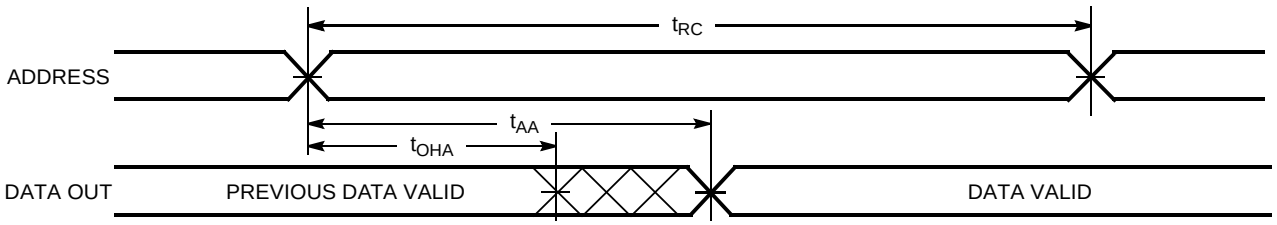
6. Full Device AC operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min.)}$ > 100 µs or stable at $V_{CC(min.)}$ > 100 µs.
7. $\overline{BHE}$.$\overline{BLE}$ is the AND of both $\overline{BHE}$ and $\overline{BLE}$. Chip can be deselected by either disabling the chip enable signals or by disabling both $\overline{BHE}$ and $\overline{BLE}$.
8. Test conditions assume signal transition time of 5 ns or less, timing reference levels of $V_{CC(typ.)}/2$, input pulse levels of 0 to $V_{CC(typ.)}$, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
9. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZBE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
10. If both byte enables are toggled together this value is 10 ns.
11. t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} transitions are measured when the outputs enter a high impedance state.
12. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$ and/or $\overline{BLE}$ = V_{IL}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.

Switching Characteristics Over the Operating Range (continued)[8]

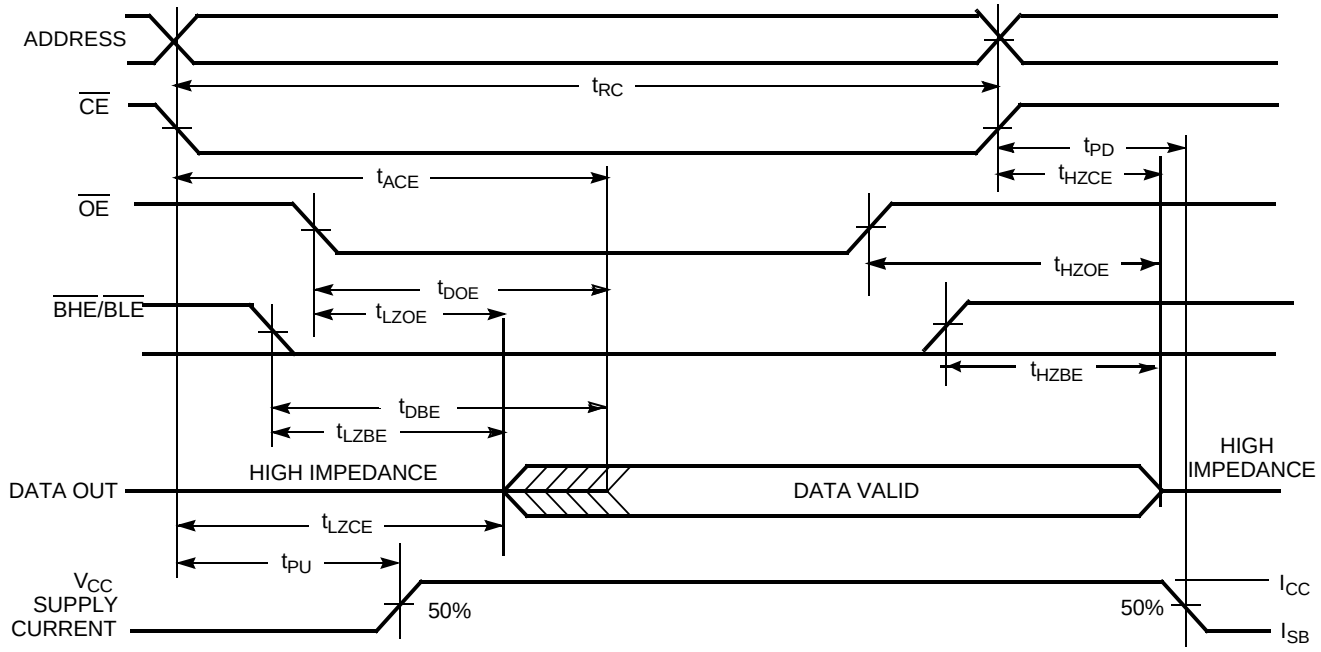
Parameter	Description	55 ns		70 ns		Unit
		Min.	Max.	Min.	Max.	
t_{AW}	Address Set-Up to Write End	45		60		ns
t_{HA}	Address Hold from Write End	0		0		ns
t_{SA}	Address Set-Up to Write Start	0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	40		50		ns
t_{BW}	$\overline{BHE}$ / $\overline{BLE}$ Pulse Width	45		60		ns
t_{SD}	Data Set-Up to Write End	25		30		ns
t_{HD}	Data Hold from Write End	0		0		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[9, 11]		25		25	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[9]	5		5		ns

Switching Waveforms

Read Cycle No. 1 (Address Transition Controlled)[13, 14]



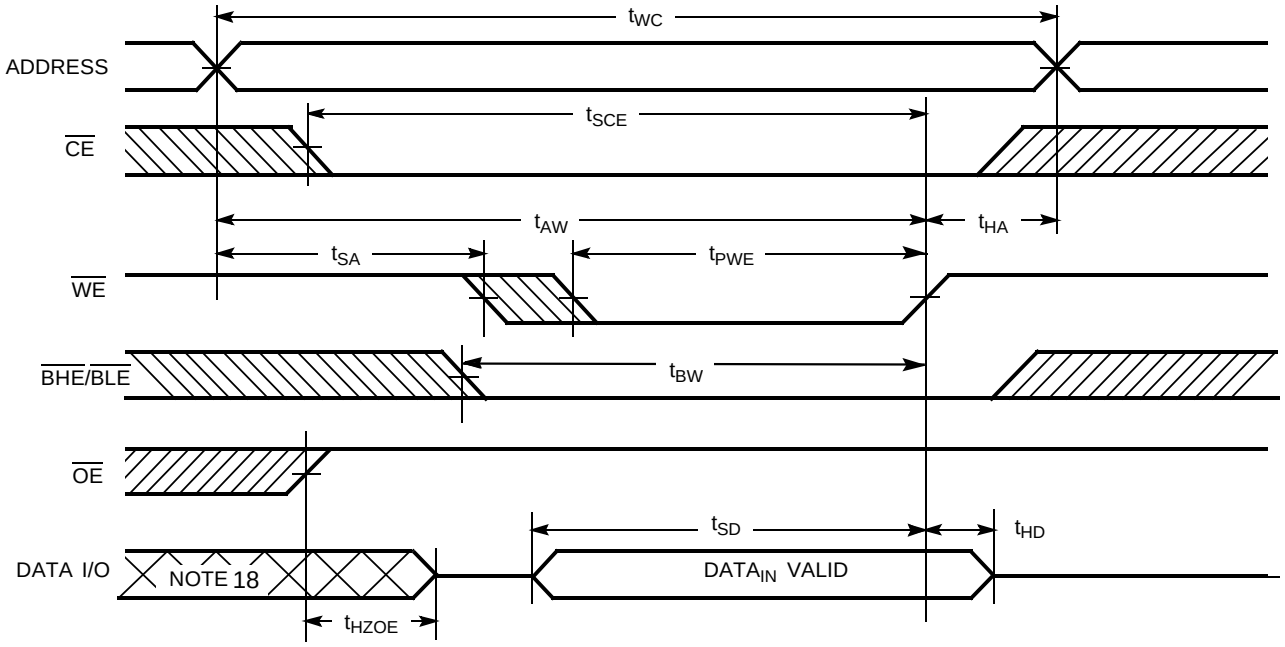
Read Cycle No. 2 ($\overline{OE}$ Controlled)[14, 15]



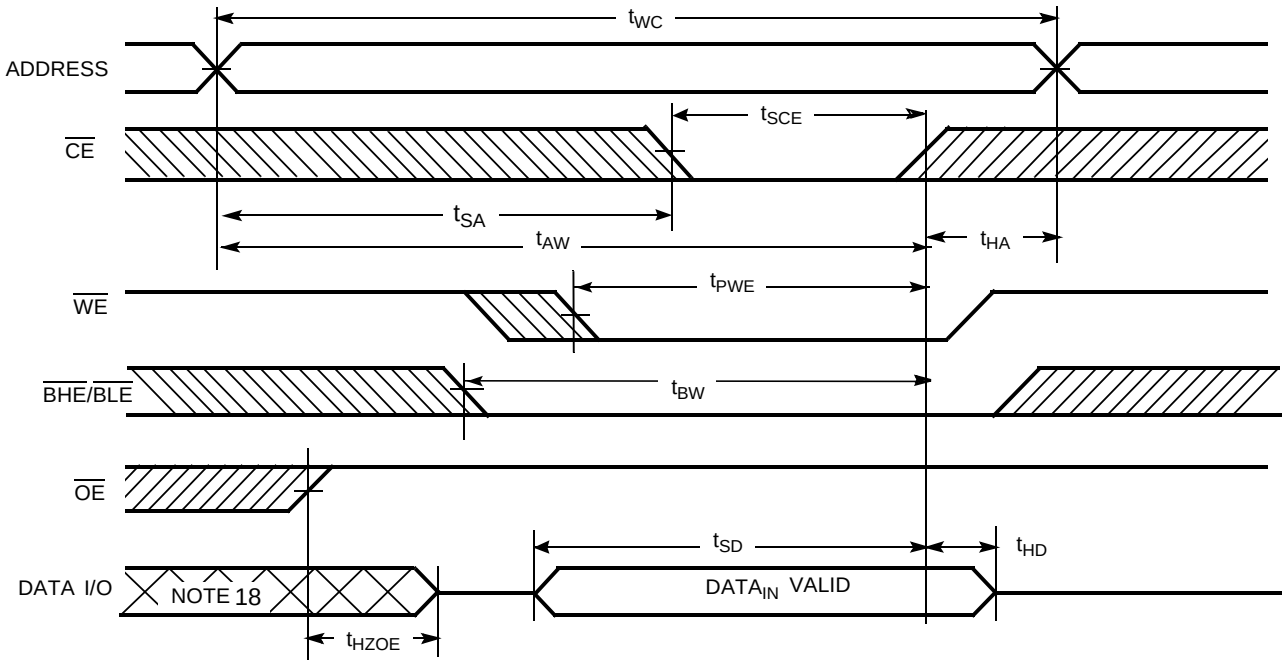
Notes:
13. Device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$, $\overline{BLE}$ = V_{IL}.
14. $\overline{WE}$ is HIGH for read cycle.
15. Address valid prior to or coincident with $\overline{CE}$, $\overline{BHE}$, $\overline{BLE}$ transition LOW.

Switching Waveforms (continued)

Write Cycle No. 1 (WE Controlled) [12, 16, 17]



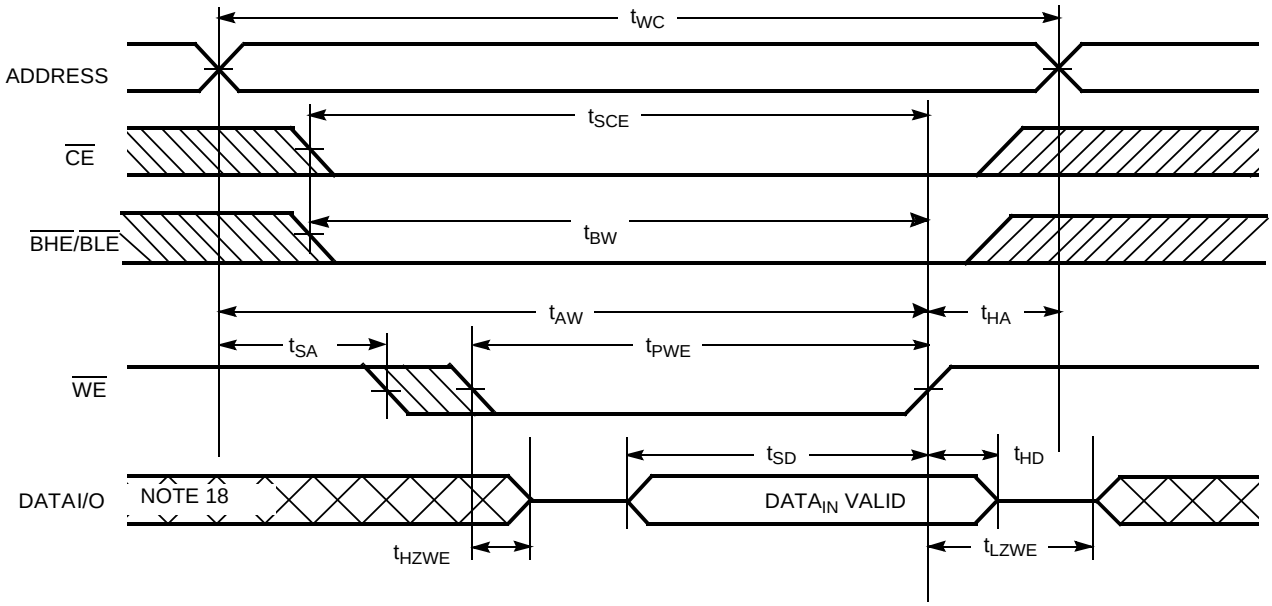
Write Cycle No. 2 (CE Controlled) [12, 16, 17]



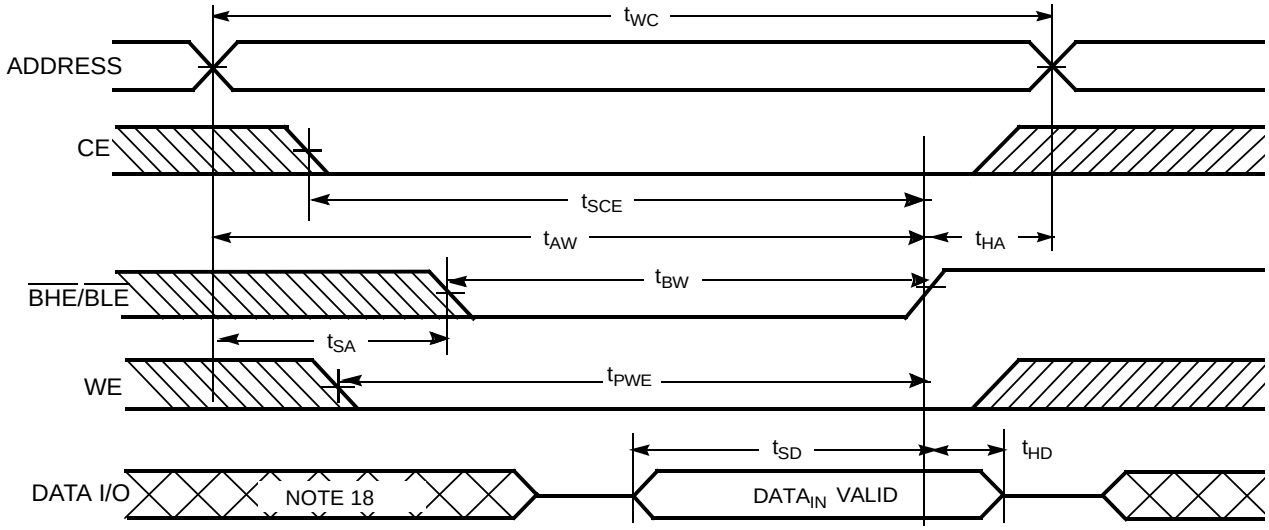
Notes:
16. Data I/O is high-impedance if $\overline{OE} = V_{IH}$.
17. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ HIGH, the output remains in a high-impedance state.
18. During this period, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)

Write Cycle No. 3 (WE Controlled, OE LOW) [17]



Write Cycle No. 4 (BHE/BLE Controlled, OE LOW) [17]



Truth Table

CE	WE	OE	BHE	BLE	Inputs/Outputs	Mode	Power
H	X	X	X	X	High Z	Deselect/Power-Down	Standby (I_{SB})
X	X	X	H	H	High Z	Deselect/Power-Down	Standby (I_{SB})
L	H	L	L	L	Data Out (I/O_O–I/O_{15})	Read	Active (I_{CC})
L	H	L	H	L	Data Out (I/O_O–I/O_7); I/O_8–I/O_{15} in High Z	Read	Active (I_{CC})
L	H	L	L	H	Data Out (I/O_8–I/O_{15}); I/O_0–I/O_7 in High Z	Read	Active (I_{CC})
L	H	H	L	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	H	L	High Z	Output Disabled	Active (I_{CC})

Truth Table (continued)

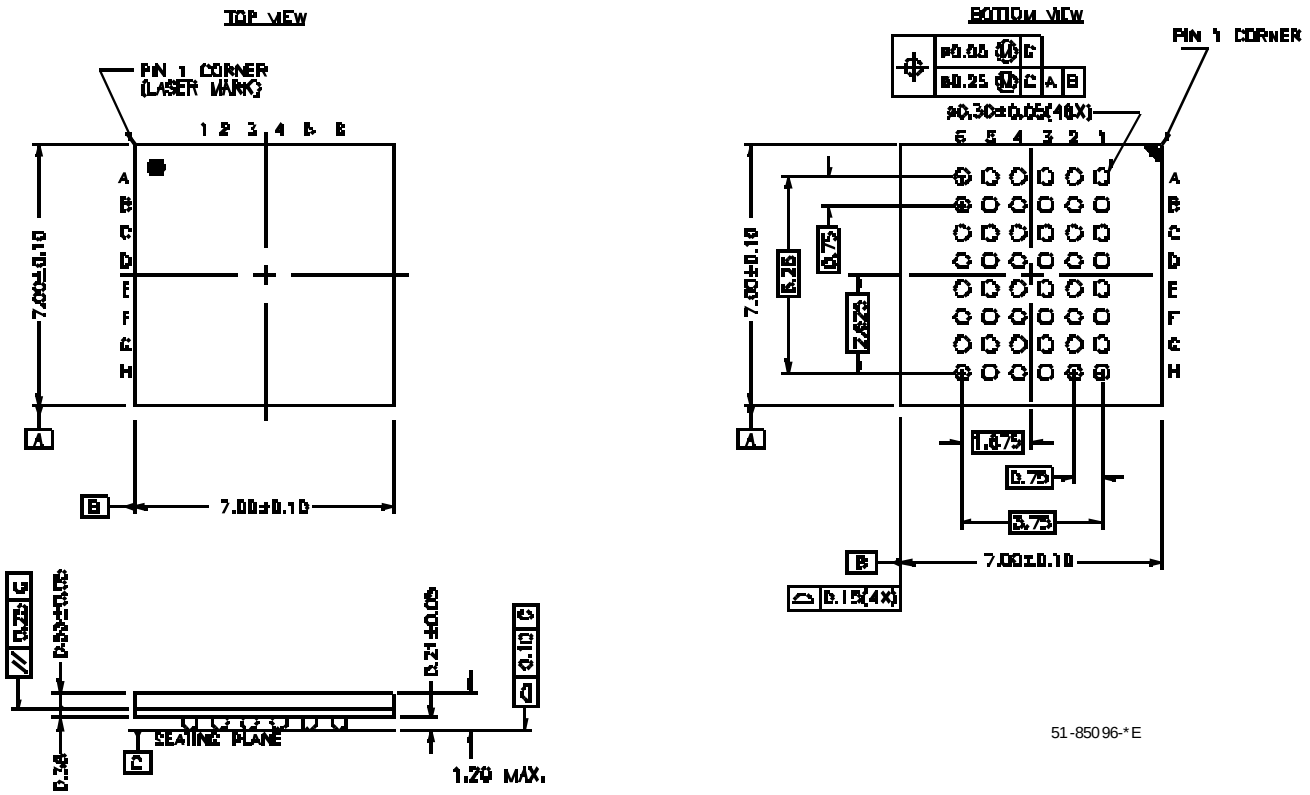
CE	WE	OE	BHE	BLE	Inputs/Outputs	Mode	Power
L	H	H	L	H	High Z	Output Disabled	Active (I_{CC})
L	L	X	L	L	Data In (I/O_O–I/O_{15})	Write	Active (I_{CC})
L	L	X	H	L	Data In (I/O_O–I/O_7)	Write Lower Byte Only	Active (I_{CC})
L	L	X	L	H	Data In (I/O_8–I/O_{15})	Write Upper Byte Only	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
55	CY62127BVLL-55ZI	Z44	44-lead TSOP II	Industrial
70	CY62127BVLL-70ZI			
	CY62127BVLL-70BAI	BA48A	48-ball Fine Pitch BGA (7 mm x 7 mm x 1.2 mm)	
	CY62127BVLL-70BVI	BV48A	48-ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	

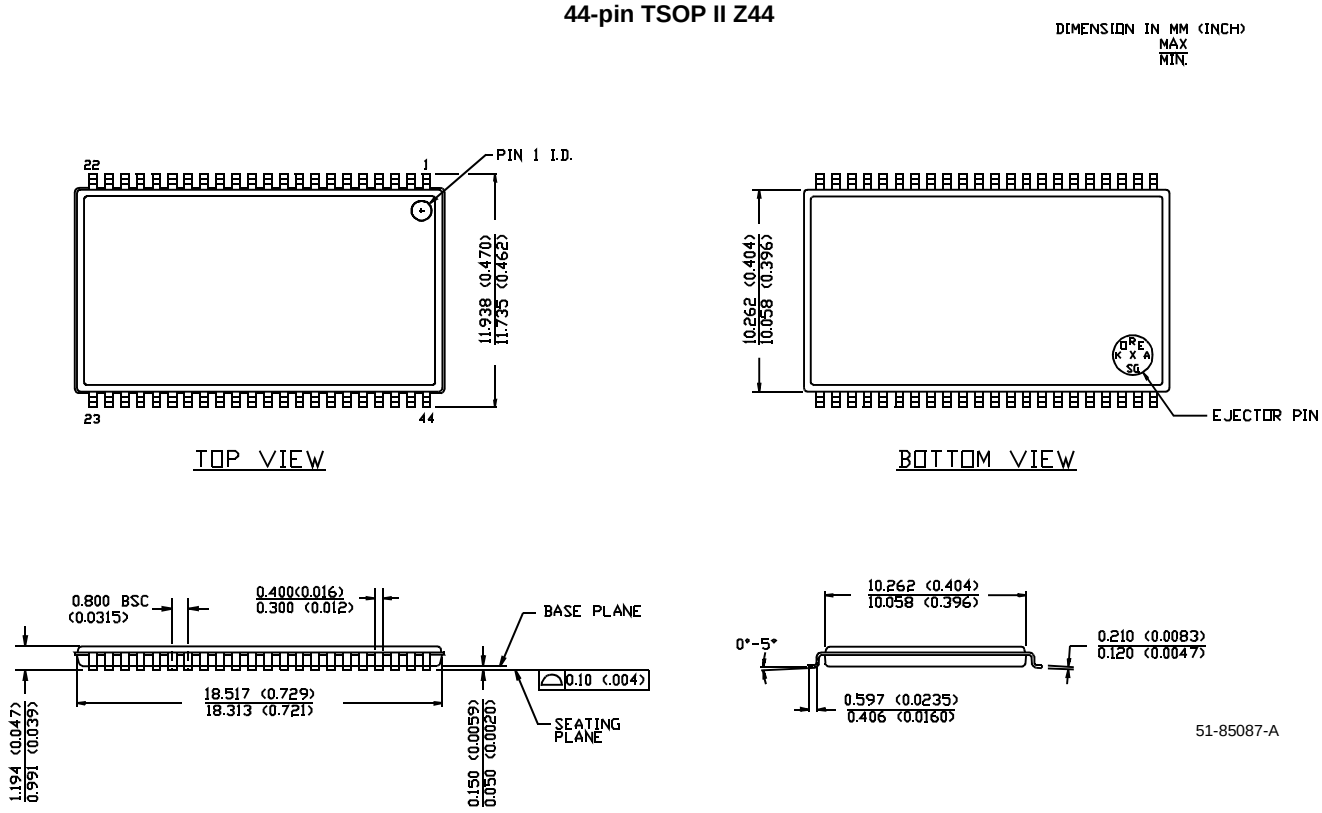
Package Diagrams

48-Ball (7.00 mm x 7.00 mm x 1.2 mm) FBGA BA48A



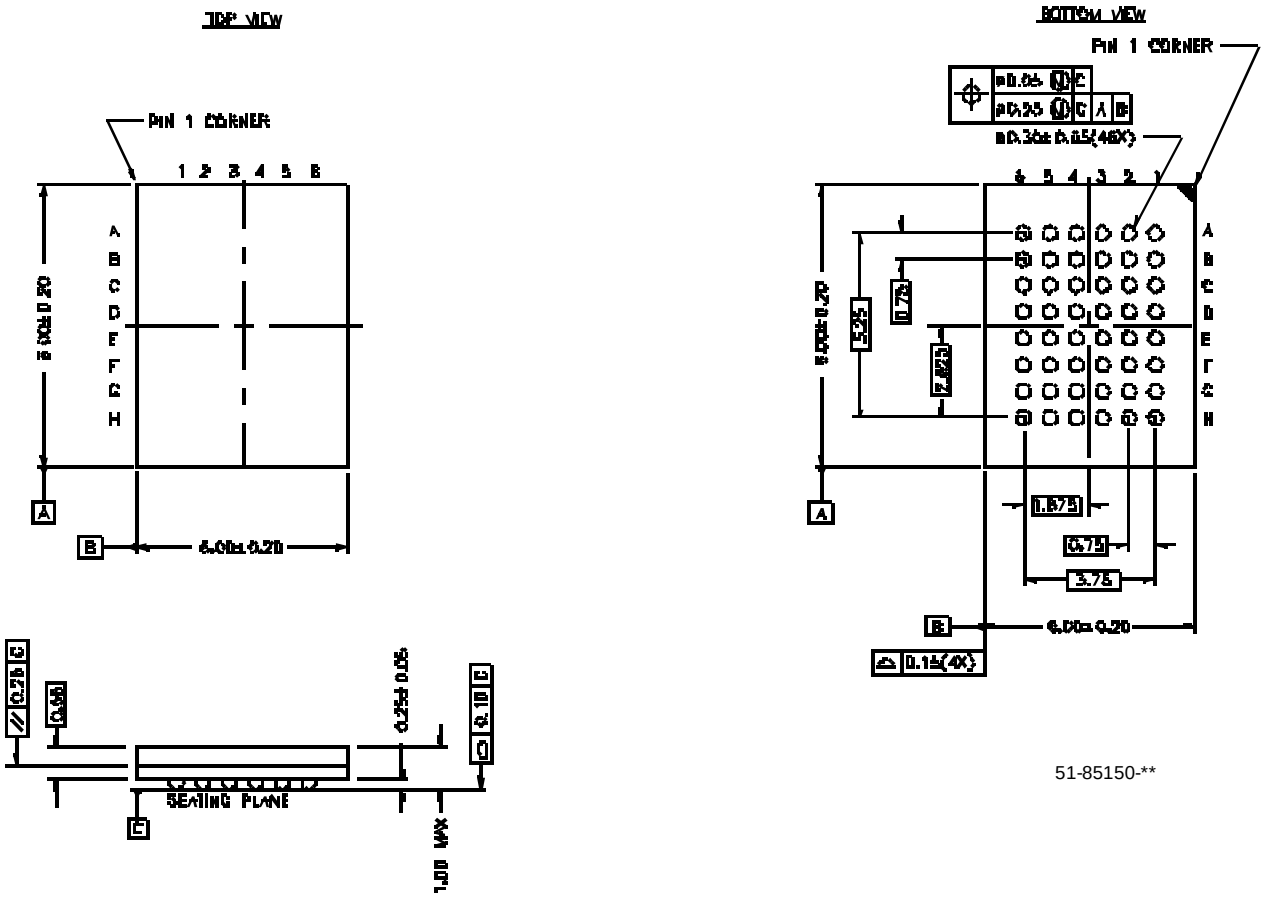
Package Diagrams (continued)

44-pin TSOP II Z44



Package Diagrams (continued)

48-Lead VFBGA (6 x 8 x 1 mm) BV48A



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Document Title: CY62127BV MoBL® 1M (64K x 16) Static RAM Document Number: 38-05155				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	109899	10/02/01	SZV	Change from Spec number: 38-01018 to 38-05155
*A	113307	03/01/02	MGN	Format standardization & update ordering information
*B	116362	09/04/02	GBI	Add footnote 1 and BV Package.